

Please amend the application as follows.

In the Claims:

Please amend the claims as follows:

In claim 4, line 1, replace "Claim 2" with -- Claim 3 --.

In claim 5, line 1, replace "Claim 4" with -- Claim 2 --.

Please cancel claims 6 through 11 without prejudice to the filing of a divisional application thereon.

REMARKS

Claims 1 through 11 are pending in this case, with this Amendment canceling claims 6 through 11 without prejudice to the filing of a divisional application thereon. The present response amends claims 4 and 5 of the application to correct typographical errors. Reconsideration and favorable action in the above-referenced application, based on the following remarks, are respectfully requested.

Rejections Under 35 U.S.C. § 102(b)

Claims 1 through 5 are rejected under 35 U.S.C. § 102(b) as being anticipated by Prengle et al. (US patent 5,171,702; hereafter, "the Prengle patent").

Claim 1 presently recites:

1. A method for fabricating a BiCMOS integrated circuit, comprising the steps of:

forming in a single implantation step a base region of a bipolar transistor and a p-well of an n-channel MOS transistor; and

forming in a single implantation step a collector contact well of a bipolar transistor and an n-well of a p-channel MOS transistor.